MSA-0600
Cascadable Silicon Bipolar MMIC Amplifier

Data Sheet

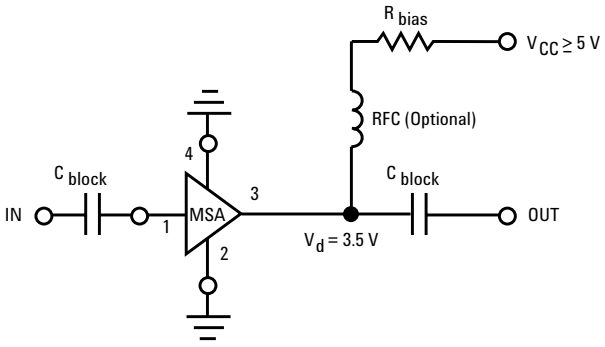
Description

The MSA-0600 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) chip. This MMIC is designed for use as a general purpose 50 W gain block. Typical applications include narrow and broad band IF and RF amplifiers in commercial, industrial and military applications.

The MSA-series is fabricated using HP's 10 GHz f_T, 25 GHz f_{MAX}, silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

The recommended assembly procedure is gold-eutectic die attach at 400°C and either wedge or ball bonding using 0.7 mil gold wire.[1] See APPLICATIONS section, "Chip Use".

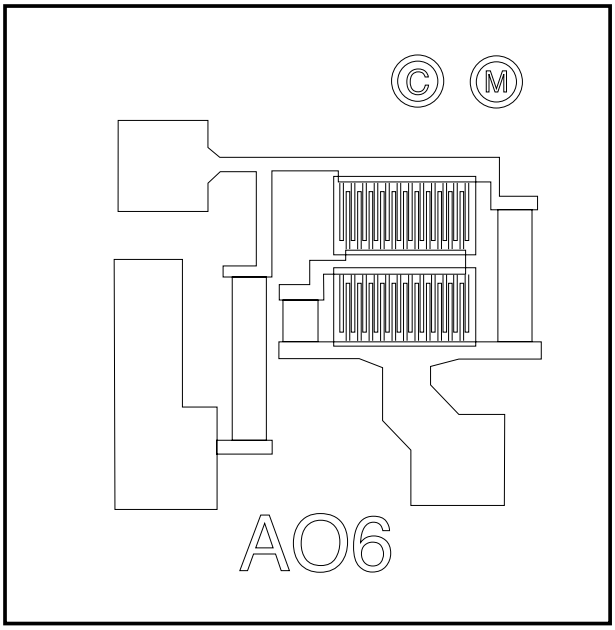
Typical Biasing Configuration



Features

- Cascadable 50 Ω Gain Block
- Low Operating Voltage (3.5 V typical V d)
- 3 dB Bandwidth: DC to 1.0 GHz
- High Gain: 19.5 dB Typical at 0.5 GHz
- Low Noise Figure: 2.8 dB Typical at 0.5 GHz

Chip Outline [1]



Note:

1. This chip contains additional biasing options. The performance specified applies only to the bias option whose bond pads are indicated on the chip outline. Refer to the APPLICATIONS section "Silicon MMIC Chip Use" for additional information.

MSA-0600 Absolute Maximum Ratings

Parameter	Absolute Maximum [1]
Device Current	50 mA
Power Dissipation [2,3]	200 mW
RF Input Power	+13 dBm
Junction Temperature	200 °C
Storage Temperature	-65 to 200 °C

Thermal Resistance [2,4] :
$\theta_{jc} = 50\,^{\circ}C/W$

Notes:
1. Permanent damage may occur if any of these limits are exceeded.
2. TMounting Surface (T_{MS}) = 25°C.
3. Derate at 20 mW/°C for TMountingÊ Surface > 190°C.
4. The small spot size of this technique results in a higher, though more accurate determination of θjc than do alternate methods. See MEASUREMENTS section "Thermal Resistance" for more information.

Electrical Specifications [1], $T_A = 25°C$

Symbol	Parameters and Test Conditions [2]: $I_d = 16$ mA, $Z_0 = 50\ \Omega$		Units	Min.	Typ.	Max.
G_P	Power Gain ($\|S_{21}\|^2$)	f = 0.1 GHz	dB		20.5	
ΔG_P	Gain Flatness	f = 0.1 to 0.6 GHz	dB		± 0.7	
$f_{3\,dB}$	3 dB Bandwidth		GHz		1.0	
VSWR	Input VSWR	f = 0.1 to 1.5 GHz			1.9:1	
	Output VSWR	f = 0.1 to 1.5 GHz			1.8:1	
NF	50 Ω Noise Figure	f = 0.5 GHz	dB		2.8	
$P_{1\,dB}$	Output Power at 1 dB Gain Compression	f = 0.5 GHz	dBm		2.0	
IP_3	Third Order Intercept Point	f = 0.5 GHz	dBm		14.5	
t_D	Group Delay	f = 0.5 GHz	psec		200	
V_d	Device Voltage		V	3.1	3.5	3.9
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-8.0	

Notes:
1. The recommended operating current range for this device is 12 to 30 mA. Typical performance as a function of current is on the following page.
2. RF performance of the chip is determined by packaging and testing 10 devices per wafer in a dual ground configuration.

Part Number Ordering Information

Part Number	Devices Per Tray
MSA-0600-GP4	100

MSA-0600 Typical Scattering Parameters[1] ($Z_O = 50\ \Omega$, $T_A = 25°C$, Id = 16 mA)

Freq.	S_{11}		S_{21}			S_{12}			S_{22}		
GHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	k
0.1	.05	-148	20.6	10.66	173	-23.3	.068	4	.05	- 67	1.05
0.2	.07	-134	20.4	10.48	166	-23.1	.070	8	.09	- 91	1.04
0.3	.09	-125	20.2	10.28	159	-22.6	.074	13	.13	-102	1.01
0.4	.11	-121	20.0	10.01	151	-22.4	.076	15	.16	-110	1.00
0.5	.13	-120	19.7	9.71	145	-22.1	.078	17	.20	-117	0.98
0.6	.15	-119	19.4	9.34	140	-21.8	.081	20	.22	-124	0.97
0.8	.19	-121	18.7	8.60	123	-20.7	.092	25	.25	-136	0.93
1.0	.25	-123	17.9	7.82	117	-19.8	.102	26	.28	-148	0.90
1.5	.32	-134	15.7	6.10	96	-18.3	.122	29	.29	-168	0.89
2.0	.40	-149	13.5	4.73	79	-17.4	.136	27	.26	175	0.91
2.5	.45	-157	11.6	3.79	70	-16.9	.142	30	.23	169	0.97
3.0	.49	-171	9.9	3.12	61	-16.6	.148	28	.19	168	1.03
3.5	.51	-174	8.3	2.60	51	-16.4	.152	25	.16	173	1.10
4.0	.51	179	6.9	2.21	43	-16.3	.153	26	.12	-170	1.22
4.5	.51	170	5.7	1.93	37	-16.0	.159	24	.10	-149	1.31
5.0	.51	162	4.7	1.71	29	-15.9	.161	24	.11	-126	1.41

Note:

1. S-parameters are de-embedded from 70 mil package measured data using the package model found in the DEVICE MODELS section.

Typical Performance, $T_A = 25°C$

(unless otherwise noted)

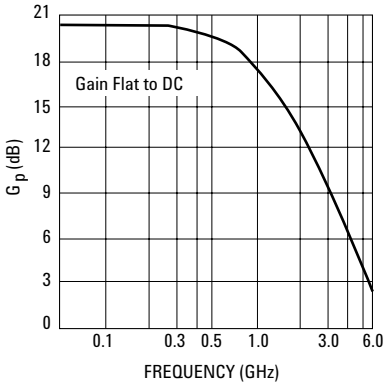


Figure 1. Typical Power Gain vs. Frequency, TA = 25°C, Id = 16 mA.

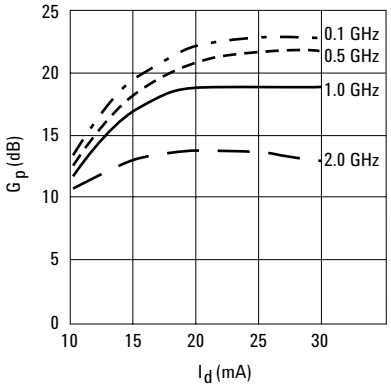


Figure 2. Power Gain vs. Current.

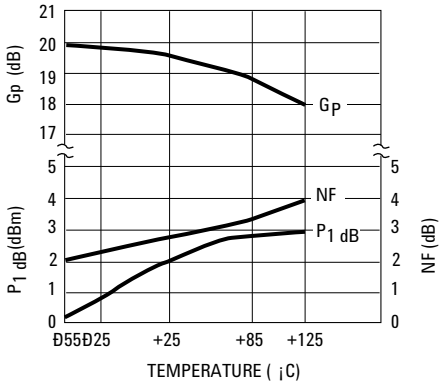


Figure 3. Output Power at 1 dB Gain Compression, NF and Power Gain vs. Mounting Surface Temperature, f = 0.5 GHz, Id = 16 mA.

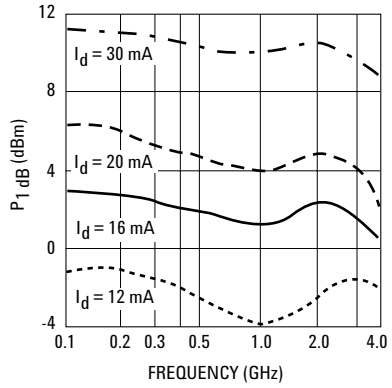


Figure 4. Output Power at 1 dB Gain Compression vs. Frequency.

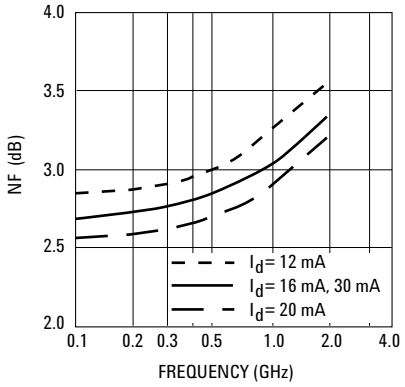
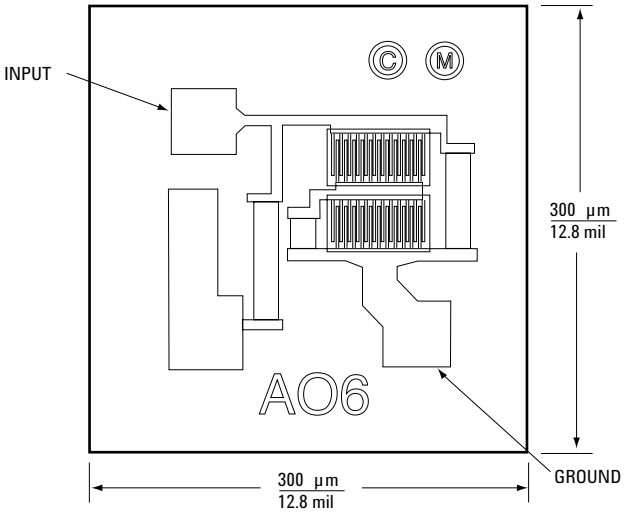


Figure 5. Noise Figure vs. Frequency.

MSA-0600 Chip Dimensions



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